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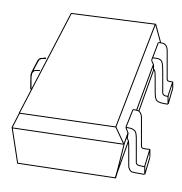
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Kind regards,

Team Nexperia

DISCRETE SEMICONDUCTORS

DATA SHEET



PBSS5140U40 V low V_{CEsat} PNP transistor

Product data sheet Supersedes data of 2001 Mar 27 2001 Jul 20



40 V low V_{CEsat} PNP transistor

PBSS5140U

FEATURES

- Low collector-emitter saturation voltage
- · High current capability
- Improved device reliability due to reduced heat generation
- Enhanced performance over SOT23 1A standard packaged transistor.

APPLICATIONS

- · General purpose switching and muting
- · LCD back lighting
- Supply line switching circuits
- Battery driven equipment (mobile phones, video cameras and hand-held devices).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT323 (SC-70) plastic package.

MARKING

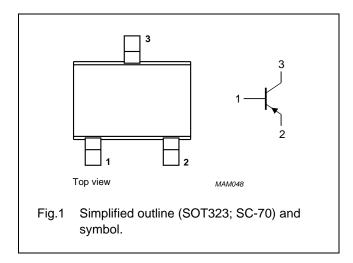
TYPE NUMBER	MARKING CODE
PBSS5140U	51t

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V _{CEO}	collector-emitter voltage	-40	V
I _{CM}	peak collector current	-2	Α
R _{CEsat}	equivalent on-resistance	<500	mΩ

PINNING

PIN	DESCRIPTION	
1	base	
2	emitter	
3	collector	



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LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V _{CBO}	collector-base voltage	open emitter	_	-40	V
V_{CEO}	collector-emitter voltage	open base	_	-40	V
V _{EBO}	emitter-base voltage	open collector	_	- 5	V
I _C	collector current (DC)		_	-1	Α
I _{CM}	peak collector current		-	-2	Α
I _{BM}	peak base current		_	-1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C; note 1	-	250	mW
		T _{amb} ≤ 25 °C; note 2	-	350	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		_	150	°C
T _{amb}	operating ambient temperature		-65	+150	°C

Notes

- 1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
R _{th j-a}	thermal resistance from junction to	in free air; note 1	500	K/W
	ambient	in free air; note 2	357	K/W

Notes

- 1. Device mounted on a printed-circuit board, single sided copper, tinplated and standard footprint.
- 2. Device mounted on a printed-circuit board, single sided copper, tinplated and mounting pad for collector 1 cm².

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CHARACTERISTICS

 T_{amb} = 25 °C unless otherwise specified.

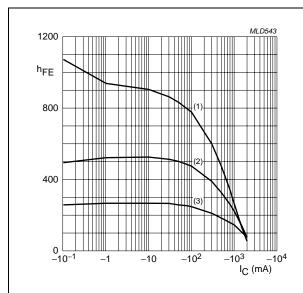
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I _{CBO}	collector-base cut-off current	$V_{CB} = -40 \text{ V}; I_{C} = 0$	_	_	-100	nA
		$V_{CB} = -40 \text{ V}; I_{C} = 0; T_{amb} = 150 ^{\circ}\text{C}$	_	_	-50	μΑ
I _{CEO}	collector-emitter cut-off current	$V_{CE} = -30 \text{ V}; I_B = 0$	_	_	-100	nA
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0$	_	_	-100	nA
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ mA}$	300	_	_	
		$V_{CE} = -5 \text{ V}; I_{C} = -100 \text{ mA}$	300	_	800	
		$V_{CE} = -5 \text{ V}; I_{C} = -500 \text{ mA}$	250	_	_	
		$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}$	160	_	_	
V _{CEsat}	saturation voltage	$I_C = -100 \text{ mA}; I_B = -1 \text{ mA}$	_	_	-200	mV
		$I_C = -500 \text{ mA}; I_B = -50 \text{ mA}$	_	_	-250	mV
		$I_C = -1 \text{ A}; I_B = -100 \text{ mA}$	_	_	-500	mV
R _{CEsat}	equivalent on-resistance	$I_C = -500 \text{ mA}$; $I_B = -50 \text{ mA}$; note 1	_	300	<500	mΩ
V _{BEsat}	base-emitter saturation voltage	$I_C = -1 \text{ A}; I_B = -50 \text{ mA}$	_	_	-1.1	V
V _{BEon}	base-emitter turn-on voltage	$V_{CE} = -5 \text{ V}; I_{C} = -1 \text{ A}$	_	_	-1	V
f _T	transition frequency	$I_C = -50 \text{ mA}; V_{CE} = -10 \text{ V};$ f = 100 MHz	150	_	_	MHz
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = I_e = 0; f = 1 \text{ MHz}$	-	=	12	pF

Note

1. Pulse test: $t_p \leq 300~\mu s;~\delta \leq 0.02.$

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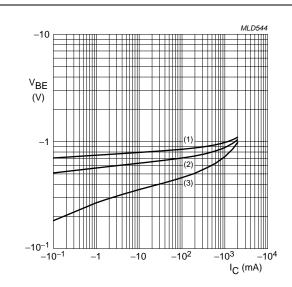
 $V_{CE} = -5 \text{ V}.$

(1) $T_{amb} = 150 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.2 DC current gain as a function of collector current; typical values.



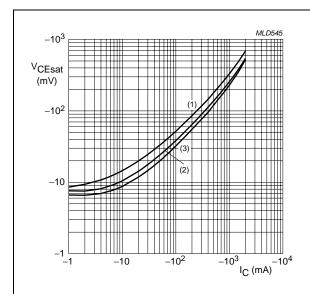
 $V_{CE} = -5 \text{ V}.$

(1) $T_{amb} = -55 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = 150 \, ^{\circ}C$.

Fig.3 Base-emitter voltage as a function of collector current; typical values.



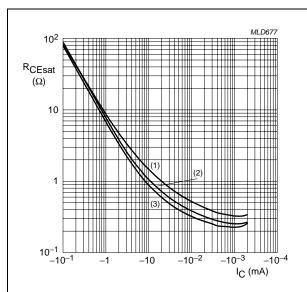
 $I_{\rm C}/I_{\rm B} = 10$.

(1) $T_{amb} = 150 \, ^{\circ}C$.

(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.4 Collector-emitter saturation voltage as a function of collector current; typical values.



 $I_{\rm C}/I_{\rm B} = 10.$

(1) $T_{amb} = 150 \, ^{\circ}C$.

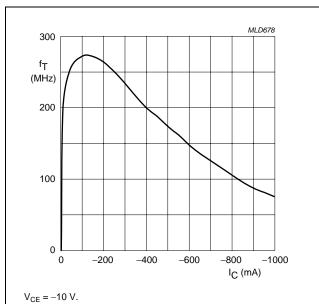
(2) $T_{amb} = 25 \, ^{\circ}C$.

(3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.5 Equivalent on-resistance as a function of collector current; typical values.

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- (1) $T_{amb} = 150 \, ^{\circ}C$.
- (2) $T_{amb} = 25 \, ^{\circ}C$.
- (3) $T_{amb} = -55 \, ^{\circ}C$.

Fig.6 Transition frequency as a function of collector current; typical values.

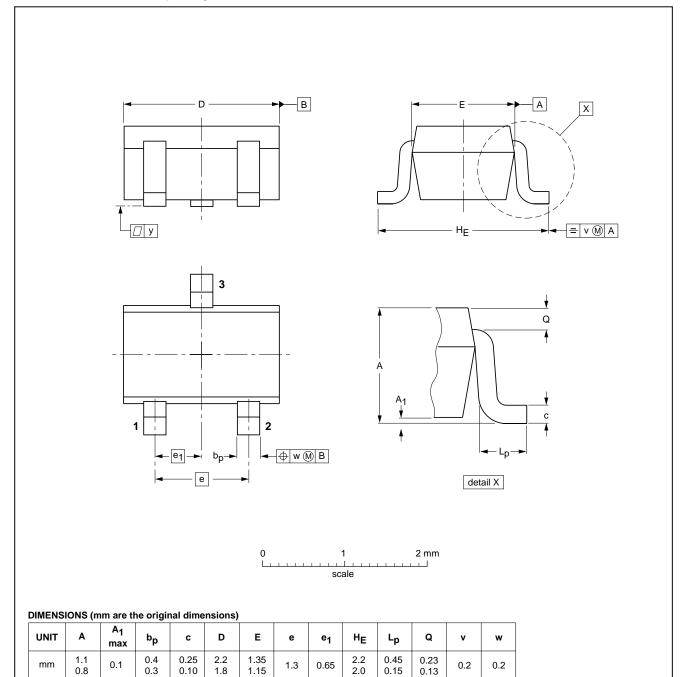
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PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT323



OUTLINE	REFERENCES		EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT323			SC-70			97-02-28

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DATA SHEET STATUS

DOCUMENT STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾	DEFINITION
Objective data sheet	Development	This document contains data from the objective specification for product development.
Preliminary data sheet	Qualification	This document contains data from the preliminary specification.
Product data sheet	Production	This document contains the product specification.

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NXP Semiconductors

Customer notification

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Contact information

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